

# BSS123L

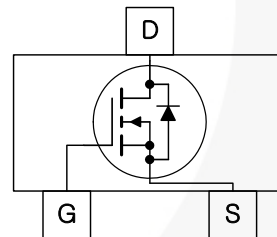
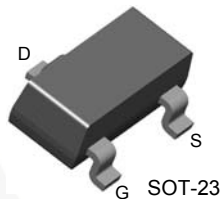
## N-Channel Logic Level Enhancement Mode Field Effect Transistor

### Features

- 0.17 A, 100 V,  $R_{DS(ON)} = 6\ \Omega$  at  $V_{GS} = 10\text{ V}$   
 $R_{DS(ON)} = 10\ \Omega$  at  $V_{GS} = 4.5\text{ V}$
- High Density Cell Design for Low  $R_{DS(ON)}$
- Rugged and Reliable
- Compact Industry Standard SOT-23 Surface Mount Package
- Very Low Capacitance
- Fast Switching Speed

### Description

This N-channel enhancement mode field effect transistor is produced using high cell density, trench MOSFET technology. This product minimizes on-state resistance while providing rugged, reliable and fast switching performance. This product is particularly suited for low-voltage, low-current applications such as small servo motor control, power MOSFET gate drivers, logic level transistor, high speed line drivers, power management/power supply and switching applications.



### Ordering Information

| Part Number | Marking | Package   | Packing Method |
|-------------|---------|-----------|----------------|
| BSS123L     | SB      | SOT-23 3L | Tape and Reel  |

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

| Symbol                         | Parameter                                                                           | Value       | Unit             |
|--------------------------------|-------------------------------------------------------------------------------------|-------------|------------------|
| $V_{\text{DSS}}$               | Drain-Source Voltage                                                                | 100         | V                |
| $V_{\text{GSS}}$               | Gate-Source Voltage                                                                 | $\pm 20$    | V                |
| $I_{\text{D}}$                 | Maximum Drain Current                                                               | Continuous  | 0.17             |
|                                |                                                                                     | Pulsed      | 0.68             |
| $T_{\text{J}}, T_{\text{STG}}$ | Operating and Storage Temperature Range                                             | -55 to +150 | $^\circ\text{C}$ |
| $T_{\text{L}}$                 | Maximum Lead Temperature for Soldering Purposes, 1/16 inch from Case for 10 Seconds | 300         | $^\circ\text{C}$ |

## Thermal Characteristics

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

| Symbol                | Parameter                                              | Value | Unit                      |
|-----------------------|--------------------------------------------------------|-------|---------------------------|
| $P_{\text{D}}$        | Maximum Power Dissipation <sup>(1)</sup>               | 0.36  | W                         |
|                       | Derate Above $25^\circ\text{C}$                        | 2.8   | mW/ $^\circ\text{C}$      |
| $R_{\theta\text{JA}}$ | Thermal Resistance, Junction-to-Ambient <sup>(1)</sup> | 380   | $^\circ\text{C}/\text{W}$ |

### Note:

- $R_{\theta\text{JA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta\text{JC}}$  is guaranteed by design while  $R_{\theta\text{CA}}$  is determined by the user's board design.



a)  $380^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

Scale 1: 1 on letter size paper

## ESD Rating<sup>(2)</sup>

| Symbol | Parameter                                        | Value | Unit |
|--------|--------------------------------------------------|-------|------|
| HBM    | Human Body Model per ANSI/ESDA/JEDEC JS-001-2012 | 50    | V    |
| CDM    | Charged Device Model per JEDEC C101C             | >2000 |      |

### Note:

- ESD values are in typical, no over-voltage rating is implied, ESD CDM zap voltage is 2000 V maximum.

## Electrical Characteristics

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

| Symbol                                                 | Parameter                                      | Conditions                                                                                   | Min.  | Typ.   | Max. | Unit                 |
|--------------------------------------------------------|------------------------------------------------|----------------------------------------------------------------------------------------------|-------|--------|------|----------------------|
| Off Characteristics                                    |                                                |                                                                                              |       |        |      |                      |
| $BV_{DSS}$                                             | Drain-Source Breakdown Voltage                 | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$                                          | 100   | 103    |      | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$                   | Breakdown Voltage Temperature Coefficient      | $I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$                            |       | 100    |      | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                                              | Zero Gate Voltage Drain Current                | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$                                                 |       | 0.027  | 1    | $\mu\text{A}$        |
|                                                        |                                                | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$                        |       | 0.159  | 60   |                      |
|                                                        |                                                | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$                                                  |       | 0.07   | 10   | nA                   |
| $I_{GSSF}$                                             | Gate-Body Leakage, Forward                     | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$                                                  |       | 0.036  | 50   | nA                   |
| $I_{GSSR}$                                             | Gate-Body Leakage, Reverse                     | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$                                                 |       | -0.019 | -50  |                      |
| On Characteristics <sup>(3)</sup>                      |                                                |                                                                                              |       |        |      |                      |
| $V_{GS(th)}$                                           | Gate Threshold Voltage                         | $V_{DS} = V_{GS}, I_D = 1\text{ mA}$                                                         | 0.8   | 1.405  | 2    | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$                 | Gate Threshold Voltage Temperature Coefficient | $I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$                                       |       | -2.82  |      | mV/ $^\circ\text{C}$ |
| $R_{DS(ON)}$                                           | Static Drain-Source On-Resistance              | $V_{GS} = 10\text{ V}, I_D = 0.17\text{ A}$                                                  |       | 2.98   | 6    | $\Omega$             |
|                                                        |                                                | $V_{GS} = 4.5\text{ V}, I_D = 0.17\text{ A}$                                                 |       | 3.17   | 10   |                      |
|                                                        |                                                | $V_{GS} = 10\text{ V}, I_D = 0.17\text{ A}, T_J = 125^\circ\text{C}$                         |       | 5.63   | 12   |                      |
| $I_{D(ON)}$                                            | On-State Drain Current                         | $V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$                                                  | 0.680 | 0.735  |      | A                    |
| $g_{FS}$                                               | Forward Transconductance                       | $V_{DS} = 10\text{ V}, I_D = 0.17\text{ A}$                                                  | 0.08  | 2.13   |      | S                    |
| Dynamic Characteristics                                |                                                |                                                                                              |       |        |      |                      |
| $C_{iss}$                                              | Input Capacitance                              | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$                              |       | 21.5   |      | pF                   |
| $C_{oss}$                                              | Output Capacitance                             |                                                                                              |       | 3.52   |      | pF                   |
| $C_{rss}$                                              | Reverse Transfer Capacitance                   |                                                                                              |       | 1.67   |      | pF                   |
| $R_G$                                                  | Gate Resistance                                | $V_{GS} = 15\text{ V}, V_{GS} = 1.0\text{ MHz}$                                              |       | 7.18   |      | $\Omega$             |
| Switching Characteristics <sup>(3)</sup>               |                                                |                                                                                              |       |        |      |                      |
| $t_{d(on)}$                                            | Turn-On Delay                                  | $V_{DD} = 30\text{ V}, I_D = 0.28\text{ A}, V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$ |       | 2.2    | 3.4  | ns                   |
| $t_r$                                                  | Turn-On Rise Time                              |                                                                                              |       | 1.7    | 18   | ns                   |
| $t_{d(off)}$                                           | Turn-Off Delay                                 |                                                                                              |       | 5.9    | 31   | ns                   |
| $t_f$                                                  | Turn-Off Fall Time                             |                                                                                              |       | 5.6    | 5    | ns                   |
| $Q_g$                                                  | Total Gate Charge                              | $V_{DS} = 25\text{ V}, I_D = 0.22\text{ A}, V_{GS} = 10\text{ V}$                            |       | 0.793  | 2.5  | nC                   |
| $Q_{gs}$                                               | Gate-Source Charge                             |                                                                                              |       | 0.092  |      | nC                   |
| $Q_{gd}$                                               | Gate-Drain Charge                              |                                                                                              |       | 0.171  |      | nC                   |
| Drain-Source Diode Characteristics and Maximum Ratings |                                                |                                                                                              |       |        |      |                      |
| $V_{SD}$                                               | Drain-Source Diode Forward Voltage             | $V_{GS} = 0\text{ V}, I_S = 440\text{ mA}^{(1)}$                                             |       | 0.867  | 1.3  | V                    |
| $T_{rr}$                                               | Diode Reverse Recovery Time                    | $I_F = 0.2\text{ A}, diF/dt = 100\text{ A}/\mu\text{S}$                                      |       | 11.9   |      | ns                   |
| $Q_{rr}$                                               | Diode Reverse Recovery Charge                  |                                                                                              |       | 1.3    |      | nC                   |

### Note:

3. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

## Typical Performance Characteristics

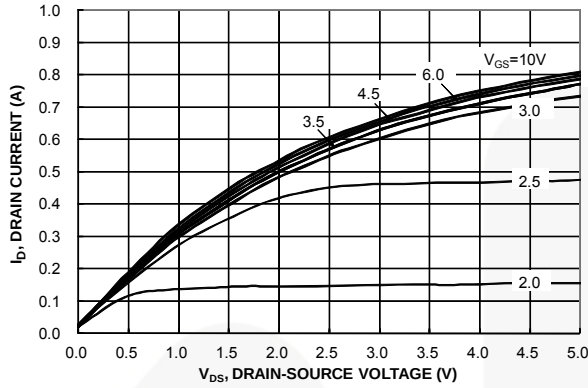


Figure 1. On-Region Characteristics

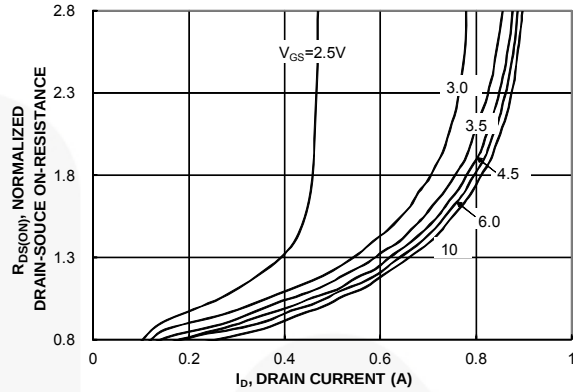


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

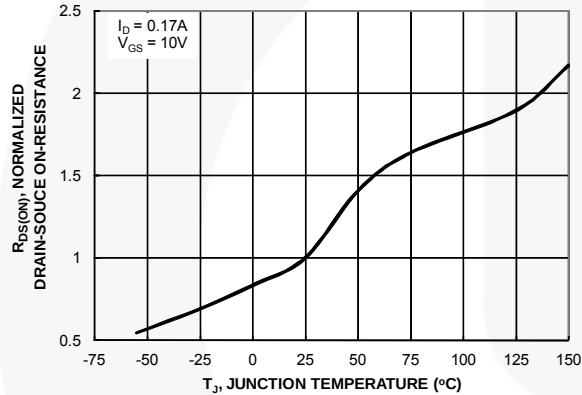


Figure 3. On-Resistance Variation with Temperature

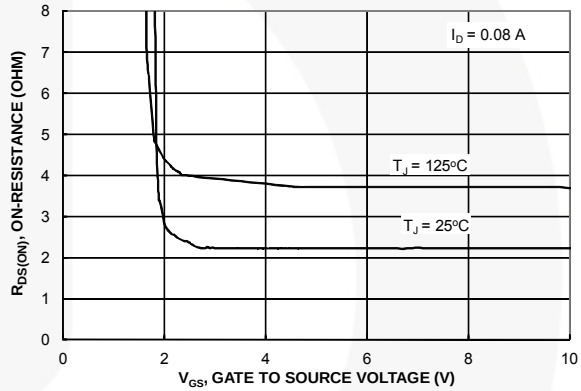


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

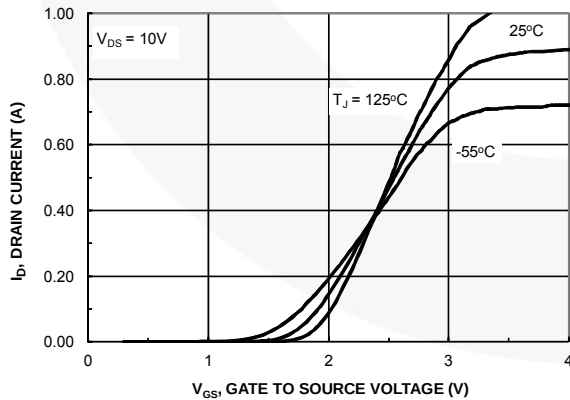


Figure 5. Transfer Characteristics

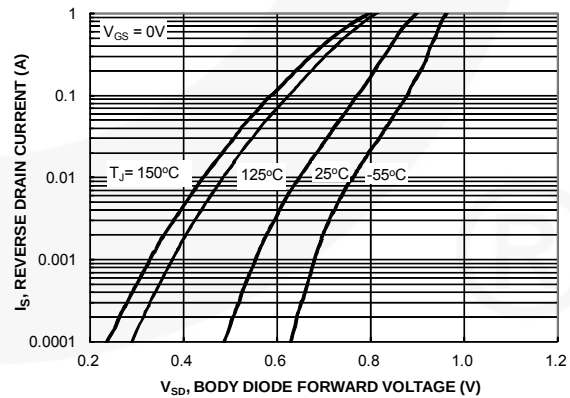


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

## Typical Performance Characteristics (Continued)

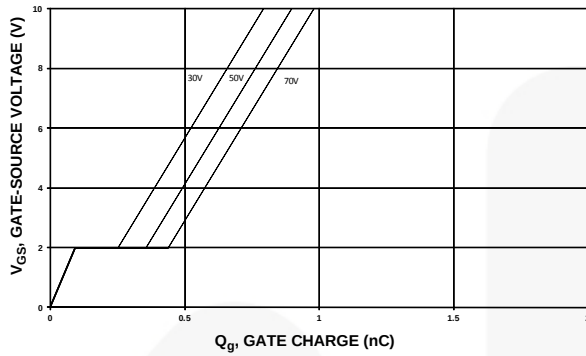


Figure 7. Gate Charge Characteristics

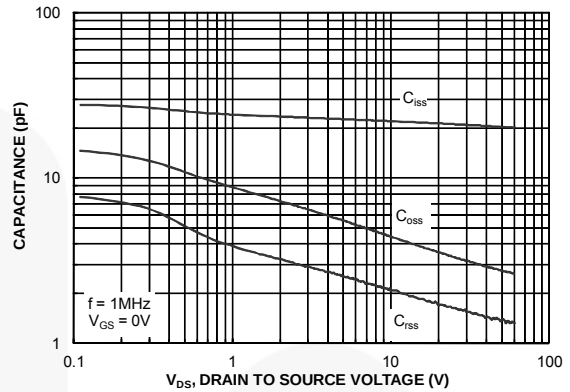


Figure 8. Capacitance Characteristics

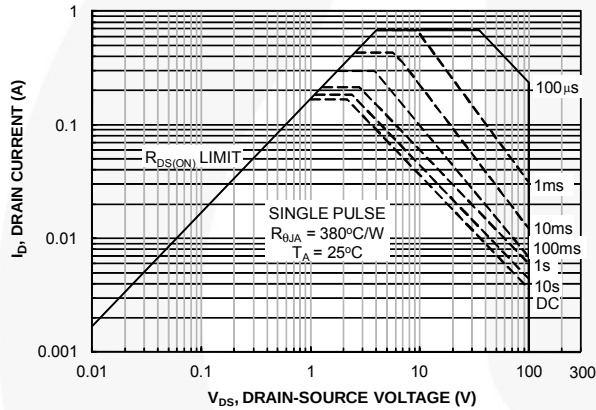


Figure 9. Maximum Safe Operating Area

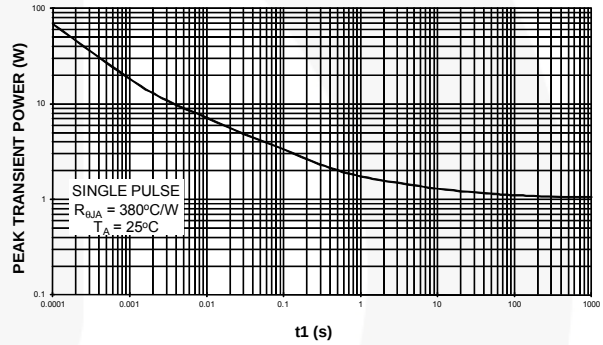


Figure 10. Single Pulse Maximum Power Dissipation

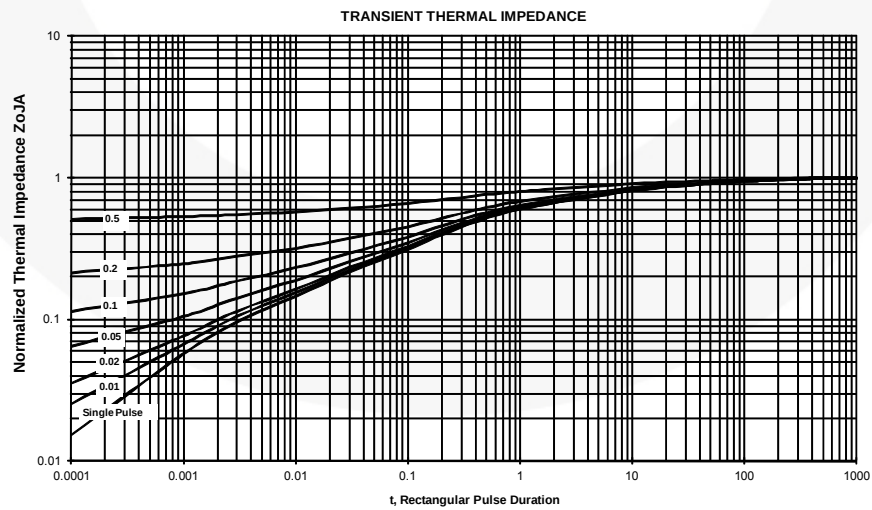
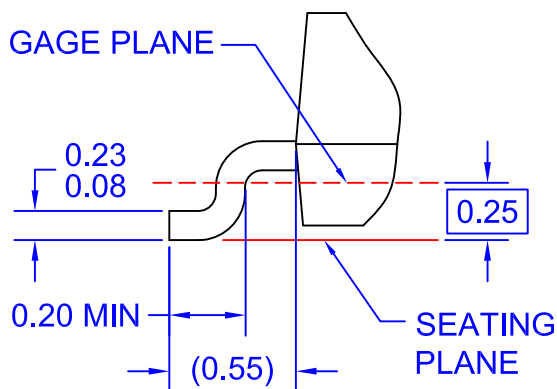
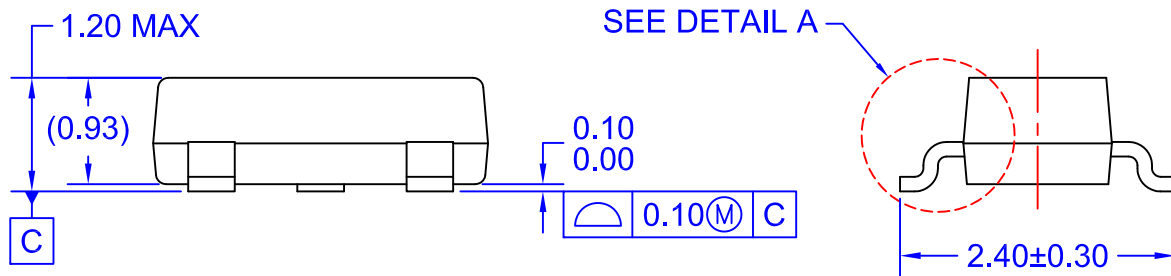
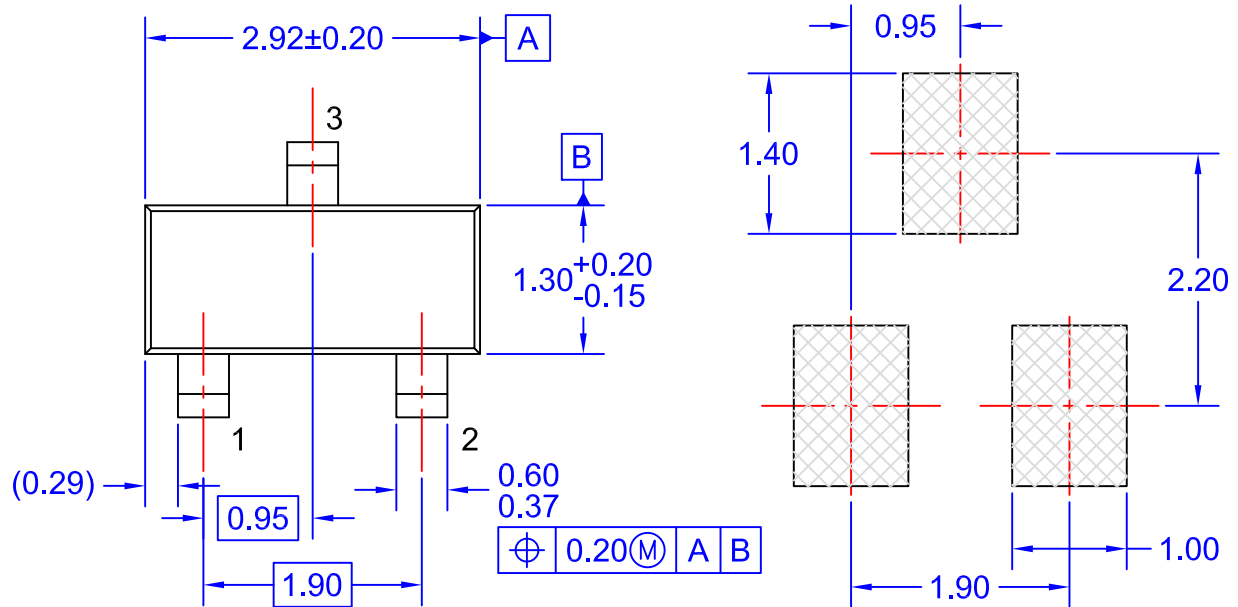


Figure 11. Transient Thermal Response Curve.



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- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
- E) DRAWING FILE NAME: MA03DREV12





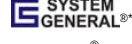
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